

Supporting Information

Nonvolatile Transistor Memory Devices using

High Dielectric Constant Polyimides Electrets

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+equal contribution to this work.

Table S1. Inherent Viscosity^a and Solubility Behavior of Polyimides

Code	η_{inh} (dL/g)	Solubility in various Solvent ^b					
		NMP	DMAc	DMF	<i>m</i> -Cresol	THF	CHCl ₃
PI(BTDA-TPA-CN)	0.97	++	++	++	++	+-	++
PI(DSDA-TPA-CN)	0.42	++	++	++	++	+-	+-
PI(6FDA-TPA-CN)	0.94	++	++	++	++	++	++

^a Measured at a polymer concentration of 0.5 g/dL in DMAc at 30 °C.

^b The solubility was determined with a 10 mg sample in 1 mL of a solvent. ++, soluble at room temperature; +, soluble on heating; +-, partially soluble or swelling.

Table S2. Thermal Properties of Polyimides^a

Polymer code	T_d^5 (°C) ^b		T_d^{10} (°C) ^b		R_{w800} (%) ^c
	N ₂	Air	N ₂	Air	
PI(BTDA-TPA-CN)	620	605	650	645	70
PI(DSDA-TPA-CN)	535	550	575	595	62
PI(6FDA-TPA-CN)	590	580	620	605	65

^a The polymer film samples were heated at 300 °C for 1 h prior to all the thermal analyses.

^b Temperature at which 5 % and 10% weight loss occurred, respectively, recorded by TGA at a heating rate of 20 °C/min and a gas flow rate of 20 cm³/min.

^c Residual weight percentages at 800 °C under nitrogen flow.

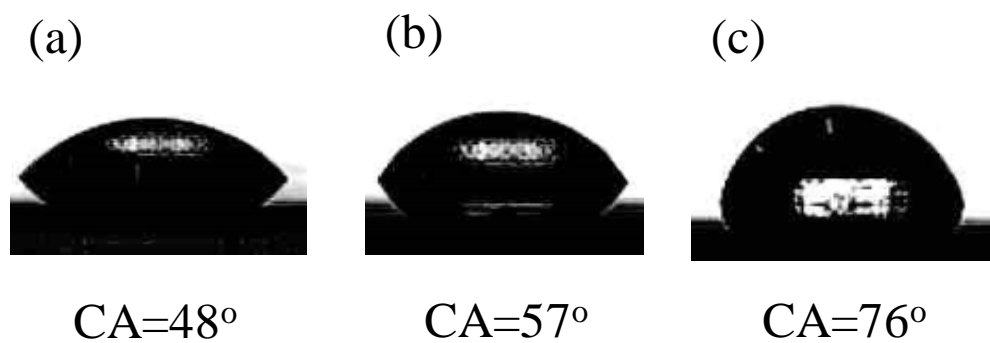


Figure S1. Contact angles of various polymer electrets: (a) **PI(BTDA-TPA-CN)**,
(b) **PI(DSDA-TPA-CN)** and (c) **PI(6FDA-TPA-CN)**.

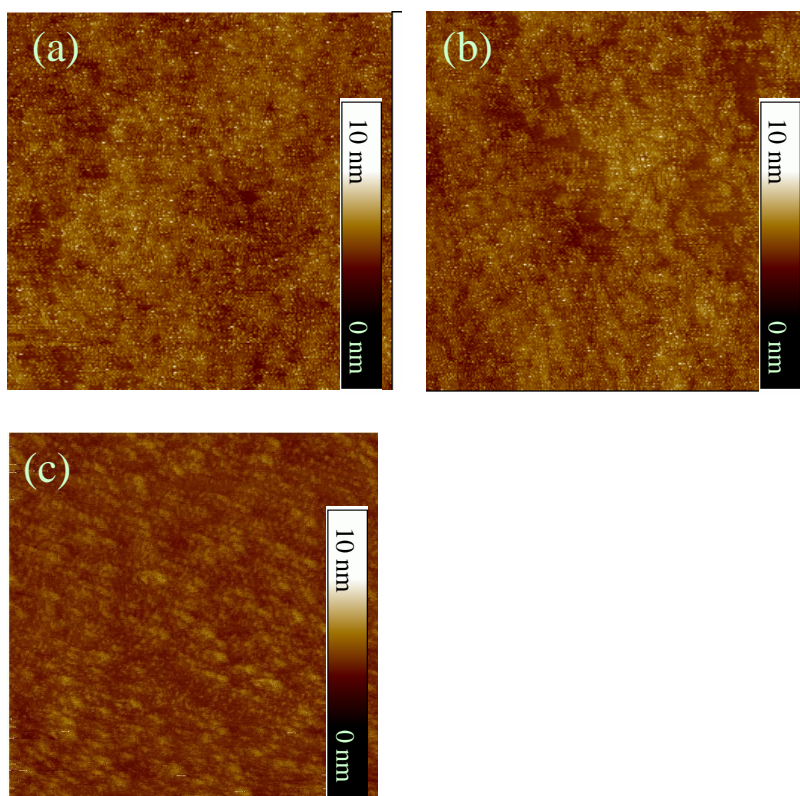


Figure S2. Atomic force microscopy (AFM) topographies of (a) **PI(BTDA-TPA-CN)**,
(b) **PI(DSDA-TPA-CN)** and (c) **PI(6FDA-TPA-CN)** spin-coated on bare SiO₂
substrates on 1 μm x 1 μm areas.

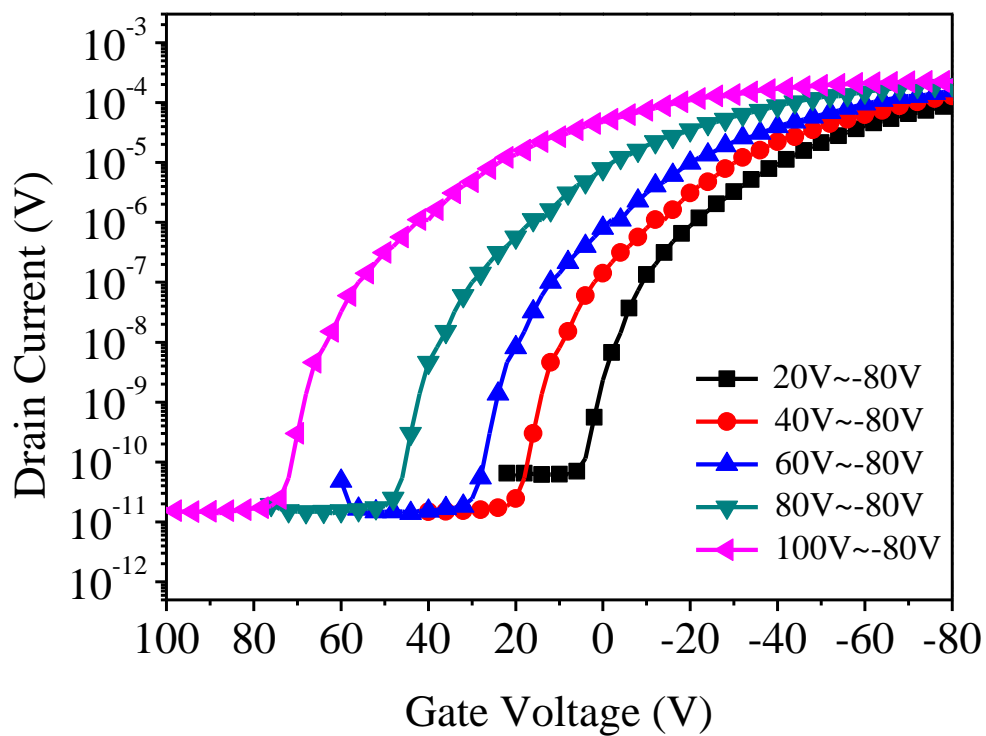


Figure S3. Transfer characteristics of the pentacene with **PI(6FDA-TPA-CN)** as electret. The V_g sweeps ranged from 20 to 100 V.

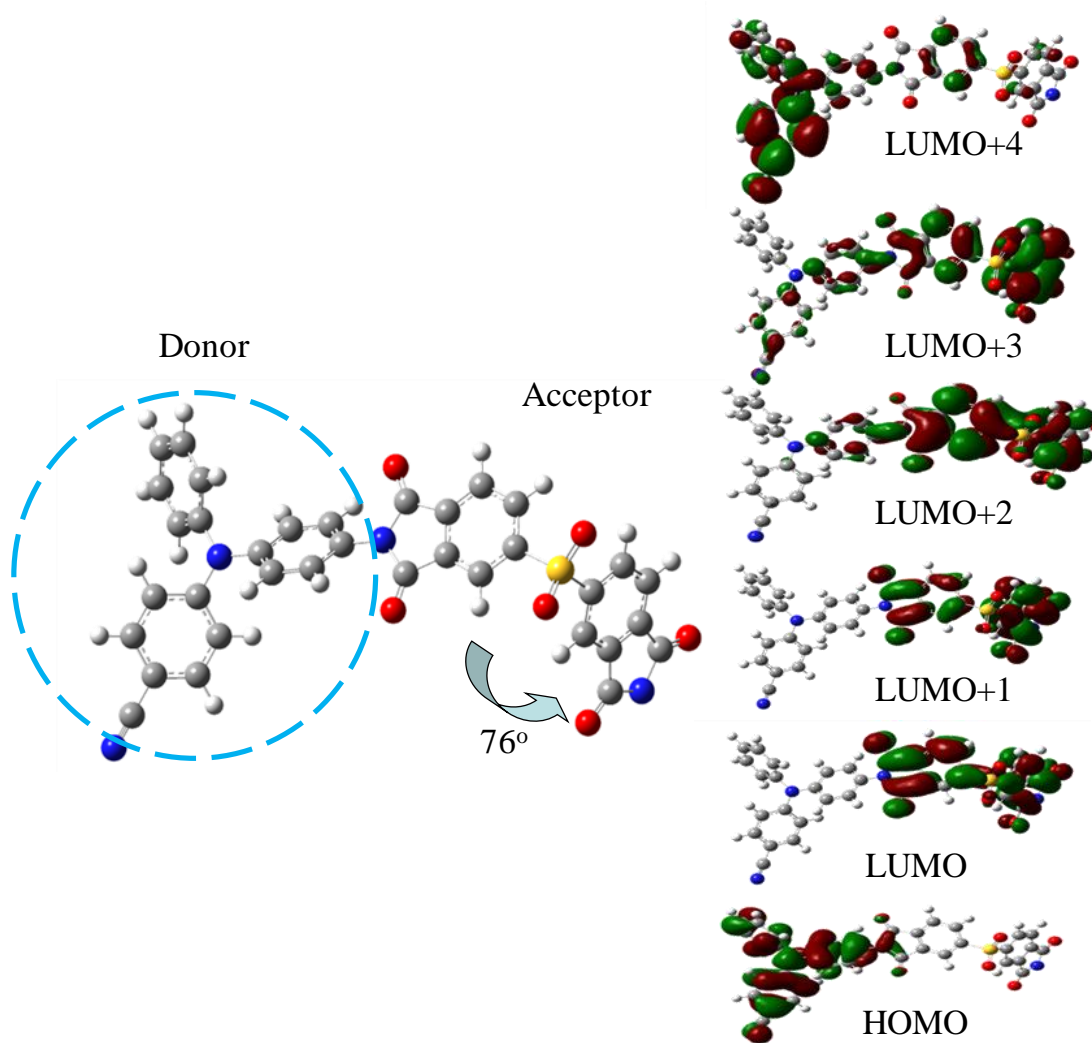


Figure S4. Molecular orbitals of PI(DSDA-TPA-CN).

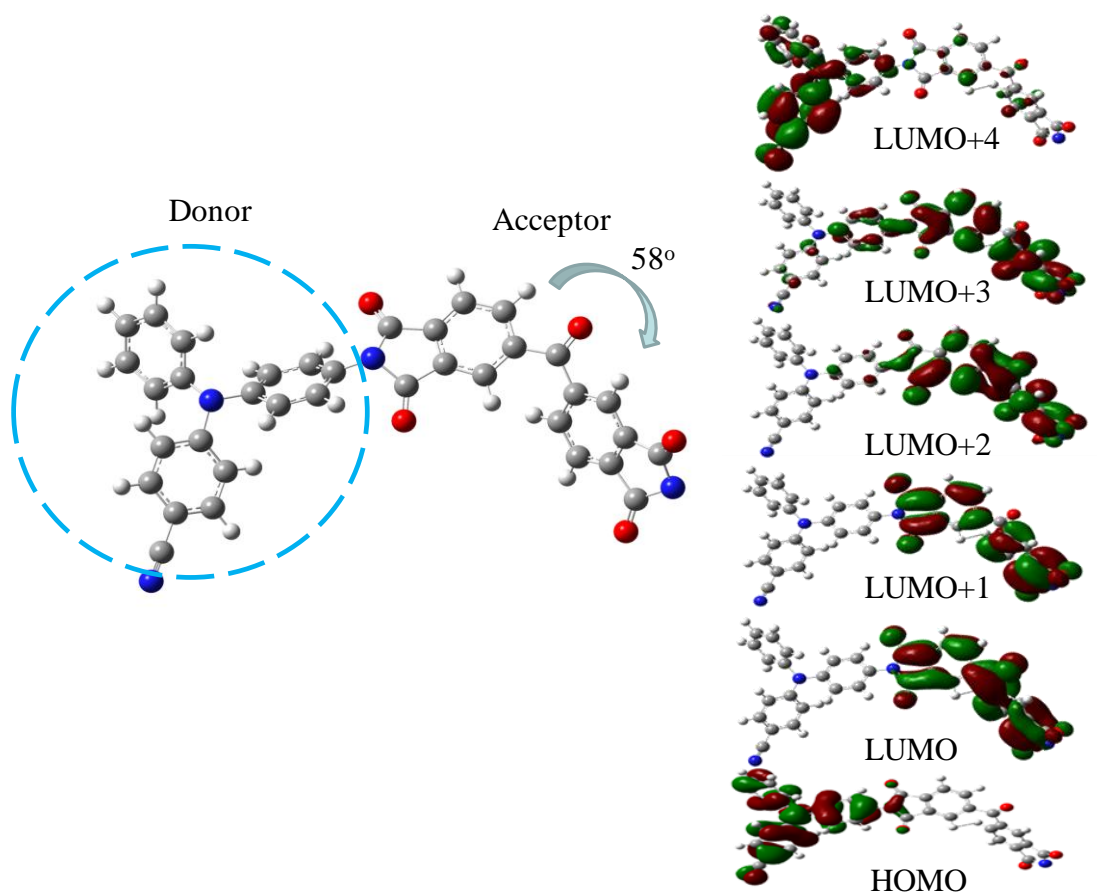


Figure S5. Molecular orbitals of PI(BTDA-TPA-CN).

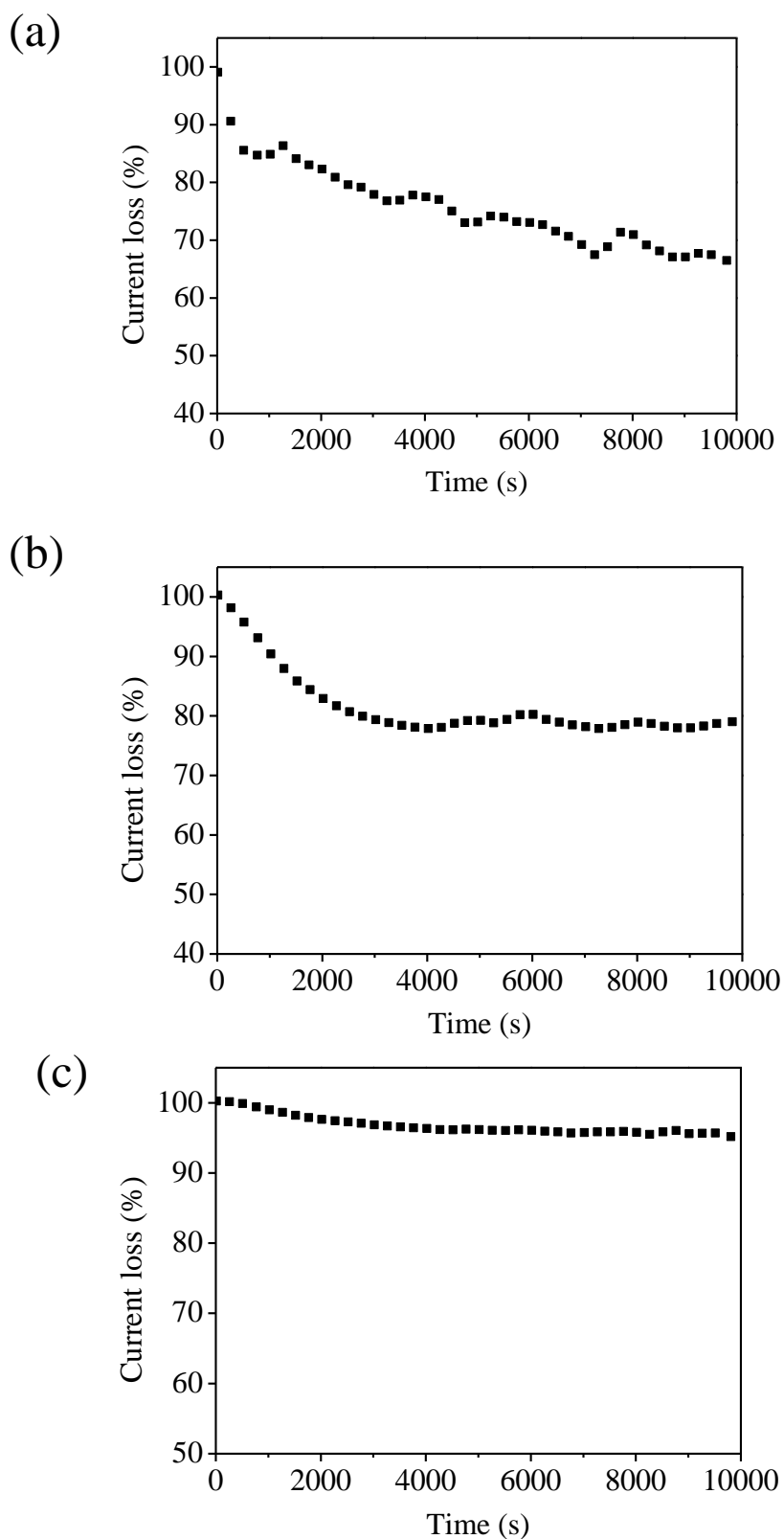


Figure S6. The on-current of OFET device decay through 10^4 s storage with (a) **PI(BTDA-TPA-CN)**, (b) **PI(DSDA-TPA-CN)** and (c) **PI(6FDA-TPA-CN)** as electrets.